CMLDM3737

SURFACE MOUNT SILICON DUAL N-CHANNEL ENHANCEMENT-MODE MOSFET



SOT-563 CASE

APPLICATIONS:

- · Load Switch / Level Shifting
- Battery Charging
- Boost Switch
- Electro-luminescent Backlighting

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLDM3737 consists of dual silicon N-Channel enhancement-mode MOSFETs designed for high speed pulsed amplifier and driver applications. These MOSFETs offer very low $r_{\mbox{DS(ON)}}$ and low threshold voltage.

MARKING CODE: 7C3

FEATURES:

- ESD Protection up to 2kV
- 350mW Power Dissipation
- Very Low r_{DS(ON)}
- Low Threshold Voltage
- · Logic Level Compatible
- Small, SOT-563 Surface Mount Package
- Complementary Dual P-Channel Device: CMLDM5757

MAXIMUM RATINGS: (TA=25°C)	SYMBOL		UNITS
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	8.0	V
Continuous Drain Current (Steady State)	ID	540	mA
Maximum Pulsed Drain Current (tp=10µs)	I_{DM}	1.5	Α
Power Dissipation (Note 1)	P_{D}	350	mW
Power Dissipation (Note 2)	P_{D}	300	mW
Power Dissipation (Note 3)	P_{D}	150	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance (Note 1)	$\Theta_{\sf JA}$	357	°C/W

ELECTRICAL SYMBOL	CHARACTERISTICS PER TRAI	NSISTOR: (T _A =25°C) MAX	UNITS
	V _{GS} =4.5V, V _{DS} =0	WIIIN	5.0	μA
I _{DSS}	V_{DS} =16V, V_{GS} =0		1.0	μΑ
BV _{DSS}	V_{GS} =0, I_{D} =250 μ A	20		V
V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.45	1.0	V
V_{SD}	V_{GS} =0, I_S =350mA		1.2	V
rDS(ON)	V_{GS} =4.5V, I_D =540mA		0.55	Ω
rDS(ON)	V_{GS} =2.5V, I_D =500mA		0.7	Ω
rDS(ON)	V_{GS} =1.8V, I_D =350mA		0.9	Ω
C _{rss}	V_{DS} =16V, V_{GS} =0, f=1.0MHz		20	pF
C _{iss}	V_{DS} =16V, V_{GS} =0, f=1.0MHz		150	pF
C _{oss}	V_{DS} =16V, V_{GS} =0, f=1.0MHz		25	pF

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm²

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⁽²⁾ FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm²

⁽³⁾ FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm²

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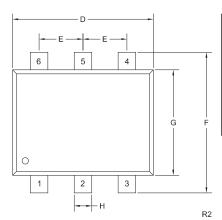


ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: $(T_A = 25^{\circ}C)$

SYMBOL	TEST CONDITIONS	ŤΥΡ	UNITS
Q _{g(tot)}	V_{DS} =10V, V_{GS} =4.5V, I_{D} =500mA	1.58	nC
Q_{gs}	V_{DS} =10V, V_{GS} =4.5V, I_{D} =500mA	0.17	nC
Q_{gd}	V_{DS} =10V, V_{GS} =4.5V, I_{D} =500mA	0.24	nC
ton	V_{DD} =10V, V_{GS} =4.5V, I_{D} =540mA, R_{G} =10 Ω	10	ns
toff	V_{DD} =10V, V_{GS} =4.5V, I_{D} =540mA, R_{G} =10 Ω	25	ns

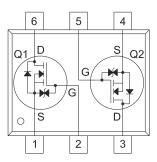
SOT-563 CASE - MECHANICAL OUTLINE





DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
Α	0.0027	0.007	0.07	0.18
В	0.008		0.20	
С	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
Е	0.020		0.50	
F	0.059	0.067	1.50	1.70
G	0.043	0.051	1.10	1.30
Н	0.006	0.012	0.15	0.30
SOT-563 (REV: R2)				

PIN CONFIGURATION



LEAD CODE:

- 1) Source Q1
- 2) Gate Q1
- 3) Drain Q2
- 4) Source Q2
- 5) Gate Q2 6) Drain Q1
- o) Diaili Qi

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